



IXFH320N10T2 Information



For Reference Only

Part Number IXFH320N10T2

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 320A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXFH320N10T2 Specifications

Manufacturer Part Number IXFH320N10T2 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series HiPerFET?, TrenchT2? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 320A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 430nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 26000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1000W (Tc) Rds On (Max) @ Id, Vgs 3.5 mOhm @ 100A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3		
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SeriesHiPerFET?, TrenchT2?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C320A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs430nC @ 10VInput Capacitance (Ciss) (Max) @ Vds26000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1000W (Tc)Rds On (Max) @ Id, Vgs3.5 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C320A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs430nC @ 10VInput Capacitance (Ciss) (Max) @ Vds26000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1000W (Tc)Rds On (Max) @ Id, Vgs3.5 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 320A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature -Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 mOhm @ 100A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Series	HiPerFET?, TrenchT2?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C320A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs430nC @ 10VInput Capacitance (Ciss) (Max) @ Vds26000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1000W (Tc)Rds On (Max) @ Id, Vgs3.5 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C320A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs430nC @ 10VInput Capacitance (Ciss) (Max) @ Vds26000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1000W (Tc)Rds On (Max) @ Id, Vgs3.5 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 mOhm @ 100A, 10V Operating Temperature Supplier Device Package TO-247AD (IXFH) Package / Case	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	320A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 26000pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 mOhm @ 100A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247-AD (IXFH) Package / Case	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1000W (Tc)Rds On (Max) @ Id, Vgs3.5 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	430nC @ 10V
FET Feature - Power Dissipation (Max) 1000W (Tc) Rds On (Max) @ Id, Vgs 3.5 mOhm @ 100A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	26000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.5 mOhm @ 100A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs3.5 mOhm @ 100A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247AD (IXFH)Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Power Dissipation (Max)	1000W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	3.5 mOhm @ 100A, 10V
Supplier Device Package TO-247AD (IXFH) Package / Case TO-247-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247AD (IXFH)
Report errors?	Package / Case	TO-247-3
		Report errors?

IXFH320N10T2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFH320N10T2 Payment Methods



















IXFH320N10T2 Shipping Methods













If you have any question about IXFH320N10T2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com